

BC 327 · BC 328

PNP SILICON AF MEDIUM POWER TRANSISTORS

THE BC327, BC328 ARE PNP SILICON PLANAR EPITAXIAL TRANSISTORS FOR USE IN AF DRIVER AND OUTPUT STAGES, AS WELL AS FOR UNIVERSAL APPLICATIONS. THE BC327, BC328 ARE COMPLEMENTARY TO THE NPN TYPE BC337, BC338 RESPECTIVELY.

CASE TO-92F

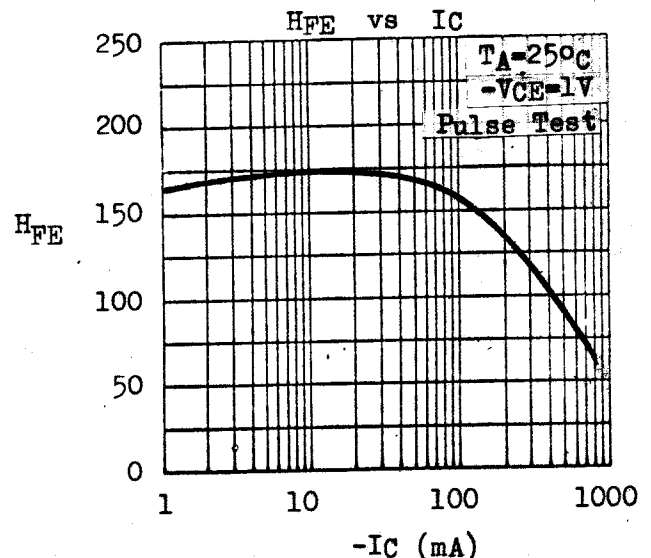
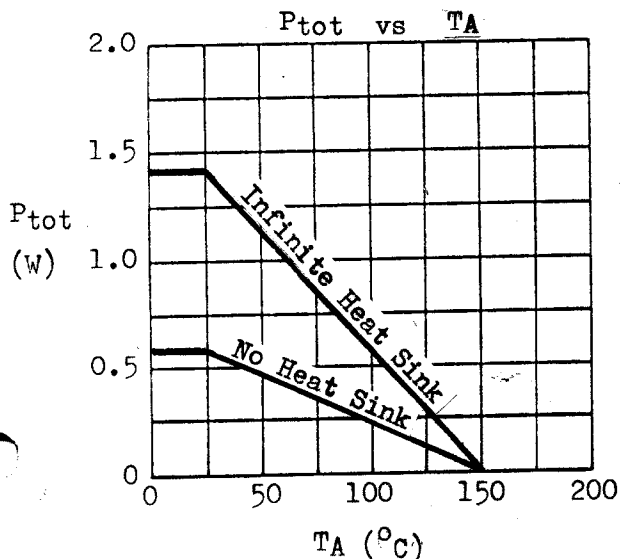


ABSOLUTE MAXIMUM RATINGS

		BC327	BC328
Collector-Emitter Voltage ($V_{BE}=0$)	- V_{CES}	50V	30V
Collector-Emitter Voltage ($I_B=0$)	- V_{CEO}	45V	25V
Emitter-Base Voltage	- V_{EBO}	5V	
Collector Current	- I_C	0.8A	
Collector Peak Current ($t \leq 10\text{ms}$)	- I_{CM}	1.5A	
Total Power Dissipation (@ $T_C \leq 25^\circ\text{C}$)	P_{tot}	1.4W	
(@ $T_A \leq 25^\circ\text{C}$)		625mW	
Operating Junction & Storage Temperature	T_j, T_{stg}	-55 to 150°C	

THERMAL RESISTANCE

Junction to Case	θ_{jc}	90°C/W	max.
Junction to Ambient	θ_{ja}	200°C/W	max.



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ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	BC327		BC328		UNIT	TEST CONDITIONS
		MIN	TYP	MAX	MIN		
Collector-Emitter Breakdown Voltage	$-BV_{CES}$	50			30	V	$-I_C=0.1\text{mA}$ $V_{BE}=0$
Collector-Emitter Breakdown Voltage	$-LV_{CEO} *$	45			25	V	$-I_C=10\text{mA}$ $I_B=0$
Emitter-Base Breakdown Voltage	$-BV_{EBO}$	5			5	V	$-I_E=0.1\text{mA}$ $I_C=0$
Collector Cutoff Current	$-I_{CES}$			100		nA	$-V_{CES}=45\text{V}$
					100	nA	$-V_{CES}=25\text{V}$
				10		10	μA
Collector-Emitter Saturation Voltage	$-V_{CE(sat)} *$		0.7		0.7	V	$-I_C=500\text{mA}$ $-I_B=50\text{mA}$
Base-Emitter Voltage	$-V_{BE} *$		1.2		1.2	V	$-I_C=300\text{mA}$ $-V_{CE}=1\text{V}$
D.C. Current Gain	$H_{FE} *$		100	630	100	630	$-I_C=100\text{mA}$ $-V_{CE}=1\text{V}$
		Group 16	100	250	100	250	
		Group 25	160	400	160	400	
		Group 40	250	630	250	630	
		All Groups	40		40		$-I_C=300\text{mA}$ $-V_{CE}=1\text{V}$
Matched Pair Ratio	$\frac{H_{FE} 1}{H_{FE} 2} *$		1.41		1.41		$-I_C=100\text{mA}$ $-V_{CE}=1\text{V}$
Current Gain-Bandwidth Product	f_T		100		100	MHz	$-I_C=10\text{mA}$ $-V_{CE}=5\text{V}$
Collector-Base Capacitance	C_{ob}		14		14	pF	$-V_{CB}=10\text{V}$ $I_E=0$ $f=1\text{MHz}$

* Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%

